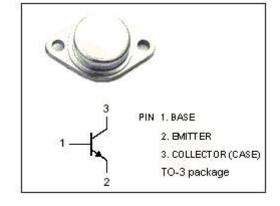


# **isc Silicon NPN Power Transistor**

MJ15003

### **DESCRIPTION**

- High DC Current Gain : h<sub>FE</sub>= 25(Min)@I<sub>C</sub>= 5A
- · Wide Area of Safe Operation
- Complement to the PNP MJ15004
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



### **APPLICATIONS**

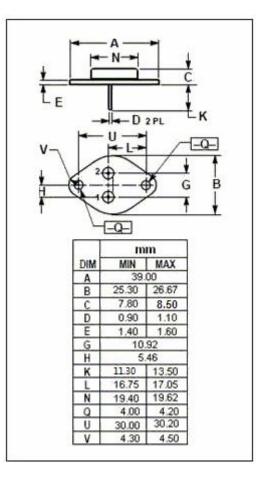
 Designed for high power audio, disk head positioners and other linear applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	140	V
V <sub>CEO</sub>	Collector-Emitter Voltage	140	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current-Continuous	20	Α
I <sub>B</sub>	Base Current-Continuous	5	Α
P <sub>D</sub>	Total Power Dissipation@Tc=25℃	250	W
Tj	Junction Temperature	200	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-65~200	${\mathbb C}$



SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	0.7	°C/W





# isc Silicon NPN Power Transistor

MJ15003

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ;I <sub>B</sub> = 0	140		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A		1	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 2V		2	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 140V; I <sub>B</sub> = 0		0.25	mA
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 140V; I <sub>E</sub> =0 V <sub>CB</sub> = 140V; I <sub>E</sub> =0;T <sub>C</sub> = 150℃		0.1 2.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		0.1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 2V	25	150	
l <sub>s/b</sub>	Second Breakdown Collector Current with Base Forward Biased	V <sub>CE</sub> = 100V,t= 1s, Nonrepetitive	1		A
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f <sub>test</sub> = 1.0MHz		1000	pF
fτ	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 10V;f <sub>test</sub> = 0.5MHz	2		MHz

## **NOTICE:**

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